

8. (Amended) A method of forming a film, comprising the steps of:
- (a) forming a film from a center region of a wafer by supplying a reaction gas at a first flow rate, while a thickness of the film is equal to or thinner than 10 nm; and
- Q2 (b) forming the film on said wafer, by starting to supply the reaction gas at a second flow rate, after said step (a), while continuing to supply the reaction gas at said first flow rate.
9. (Amended) The method according to claim 8, wherein said first flow rate is in a range of one fifth to one tenth of said second flow rate.
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